MP6533



The Future of Analog IC Technology

DESCRIPTION

The MP6533 is a gate driver IC designed for three-phase brushless DC motor driver applications. It is capable of driving three half bridges consisting of six N-channel power MOSFETs up to 60V.

The MP6533 uses a bootstrap capacitor to generate a supply voltage for the high-side MOSFET driver. An internal trickle-charge circuit maintains sufficient gate driver voltage at 100% duty cycle.

Internal safety features include programmable over-current protection, a motor start-up current limit, adjustable dead-time control, UVLO, and thermal shutdown.

The device has three Hall-element inputs. Commutation logic is determined by three Hallelement inputs spaced at 120°. The PWM, DIR, and nBRAKE inputs are used to control motor speed, direction, and brake engagement.

The MP6533 is available in a 28-pin 9.7mm x 6.4mm TSSOP with an exposed thermal pad.

FEATURES

- Wide 5V to 60V Input Voltage Range
- Hall Signal Interface
- Bootstrap Gate Driver with Trickle-Charge Circuit Supports 100% Duty Cycle Operation
- Low-Power Sleep Mode for Battery-Powered Applications
- Programmable Over-Current Protection of External MOSFETs
- Adjustable Dead-Time Control to Prevent Shoot-Through
- PWM Speed-Control Input
- Brake Input
- Motor Start-Up Current Limit
- Thermal Shutdown and UVLO Protection
- Fault Indication Output
- Thermally Enhanced Surface-Mount Package

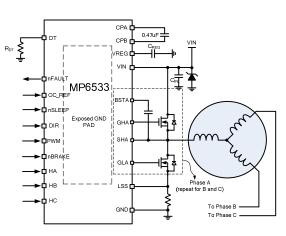
APPLICATIONS

- Three-Phase Brushless DC Motors and Permanent Magnet Synchronous Motors
- Power Drills
- Impact Drivers
- E-Bike

All MPS parts are lead-free, halogen-free, and adhere to the RoHS directive. For MPS green status, please visit the MPS website under Quality Assurance.

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TYPICAL APPLICATION



MP6533 Rev.1.1 7/3/2015 www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2015 MPS. All Rights Reserved.



ORDERING INFORMATION

Part Number*	Package	Top Marking
MP6533GF	TSSOP-28 EP	See Below

* For Tape & Reel, add suffix -Z (e.g. MP6533GF-Z);

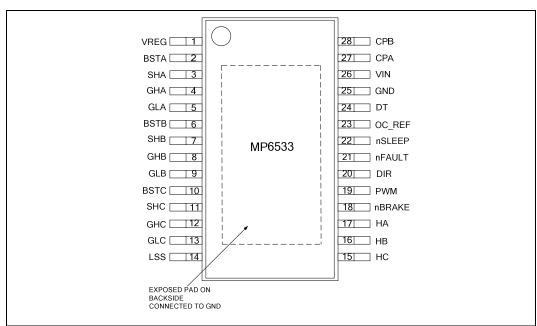
TOP MARKING

MPSYYWW

MP6533

LLLLLLLL

MPS: MPS prefix: YY: year code; WW: week code: MP6533: part number; LLLLLLLL: lot number;



PACKAGE REFERENCE



ABSOLUTE MAXIMUM RATINGS (1)

Input Voltage V _{IN}	0.3V to 65V
CPA	0.3V to 60V
СРВ	0.3V to 12.5V
VREG	0.3V to 13V
BSTA/B/C	
GHA/B/C	0.3V to 70V
SHA/B/C	0.3V to 65V
GLA/B/C	0.3V to 13V
LSS	0.3V to 1V
All Other Pins to AGND	
Continuous Power Dissipation	ו (T _A = +25°C) ⁽²⁾
TSSOP-28 EP	3.9W
Storage Temperature	55°C to +150°C
Junction Temperature	+150°C
Lead Temperature (Solder)	+260°C

Recommended Operatin	g Con	ditions ⁽³⁾
Input Voltage V _{IN}		5V to 60V
OC_REF Voltage Voc	0.1	25V to 2.4V
Operating Junct. Temp (T_J)	- 40°	C to +125°C
Thermal Resistance ⁽⁴⁾	θ _{JA}	$\boldsymbol{\theta}_{JC}$

TSSOP-28 EP326°C/W

Notes:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction temperature T_J (MAX), the junction-toambient thermal resistance θ_{JA} , and the ambient temperature T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D (MAX) = (T_J (MAX)-T_A)/ θ_{JA} . Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.



ELECTRICAL CHARACTERISTICS

 $V_{IN} = 24V$, $T_A = 25^{\circ}C$, unless otherwise noted.

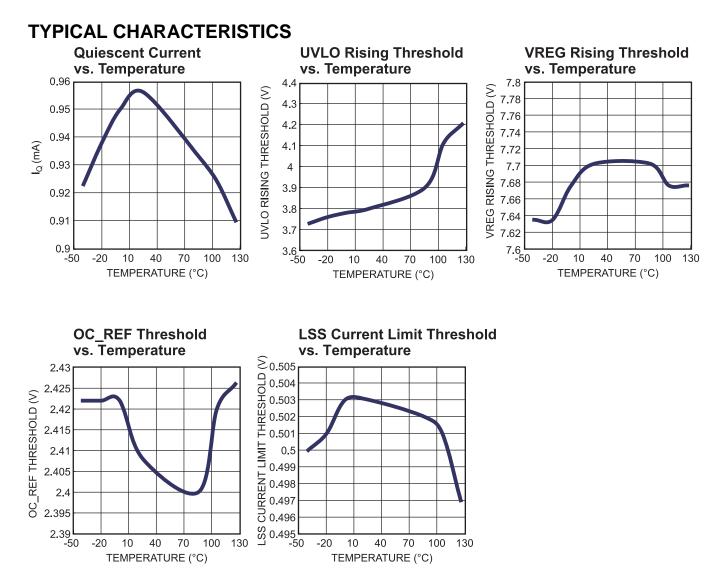
Parameter	Symbol	Condition	Min	Тур	Max	Units
Power Supply						
Input Supply Voltage	V _{IN}		5		60	V
Quiescent Current	Ι _Q	nSLEEP=1, gate not switching		0.95	2	mA
	I _{SLEEP}	nSLEEP=0			1	μA
Control Logic				•		
Input Logic 'Low' Threshold	VIL				0.8	V
Input Logic 'High' Threshold	V _{IH}		2			V
Logic Input Current	I _{IN(H)}	V _{IH} =5V	-20		20	μA
	I _{IN(L)}	V _{IL} =0.8V	-20		20	μA
nSLEEP Pull Down Current	I _{SLEEP-PD}			1		μA
Internal Pull Down Resistance	R_{PD}			880		kΩ
Fault Outputs(Open-Drain C	Outputs)					
Output Low Voltage	V _{OL}	I _o =5mA			0.5	V
Output High Leakage Current	I _{OH}	V ₀ =3.3V			1	μA
Protection Circuit		1				
UVLO Rising Threshold	V _{IN RISE}		3.3	3.9	4.5	V
UVLO Hysteresis	V _{IN HYS}			200		mV
VREG Rising Threshold	V _{REG RISE}		6.8	7.6	8.4	V
VREG Hysteresis	V _{REG HYS}			0.54	1	V
VREG Startup Delay	t _{REG}			700		μs
		V _{OC} =1V, T _J =25°C	0.8	1	1.2	V
OC_REF Threshold	V _{oc}	V _{OC} =2.4V, T _J =25°C	2.18	2.4	2.62	V
OCP Deglitch Time	t _{oc}			3		μs
SLEEP Wakeup Time	t _{SLEEP}			1		ms
LSS Current Limit Threshold	V_{LSS}		0.4	0.5	0.6	V
LSS Current Limit Fixed Off Time	t _{OFF}		53	66	80	us
LSS Current Limit High side Minimum On Time	t _{on}			1		us
Thermal Shutdown	T _{TSD}			150		°C



ELECTRICAL CHARACTERISTICS (continued) $V_{IN} = 24V$, $T_A = 25^{\circ}C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Gate Drive		·				
Bootstrap Diode Forward	V	I _D =10mA			0.9	V
Voltage	V_{FBOOT}	I _D =100mA			1.3	V
VREG Output Voltage	V _{REG}	V _{IN} =5.5V-60V T _{.1} =25°C	10	11.5	12.8	
VREG Oulput Voltage	♥ REG	V _{IN} =5V	2xV _{IN} -1			V
Gate Drive Pull Up Resistance	R_{UP}	V _{DS} =1V		8		Ω
HS Gate Drive Pull Down Resistance	$R_{HS ext{-}DN}$	V _{DS} =1V	1.2		4.3	Ω
LS Gate Drive Pull Down Resistance	$R_{LS\text{-}DN}$	V _{DS} =1V	1		5	Ω
LS Passive Pull Down Resistance	R_{LS-PDN}			590		kΩ
LS Automatic Turn On Time	t _{LS}			1.8		μs
Charge Pump Frequency	f _{CP}			110		kHz
		Leave DT Open		6		μs
Dead Time	t _{DEAD}	R _{DT} =200kΩ		0.74		μs
		DT tied to GND		30		ns

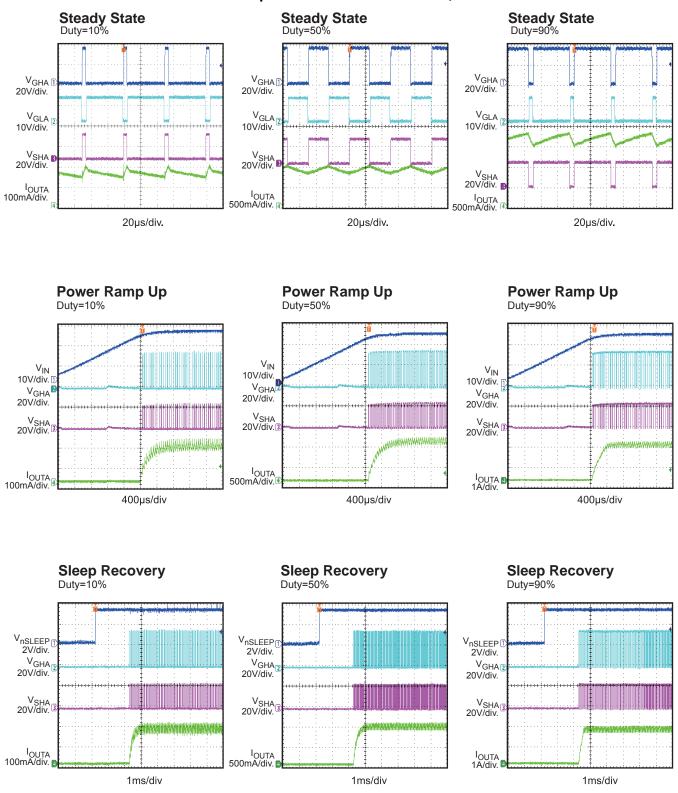






TYPICAL PERFORMANCE CHARACTERISTICS

 V_{IN} =24V, OC_REF=0.5V, R_{DT} =200k, DIR=H, HA=HC=H, HB=L, F_{PWM} =20kHz, T_A =25°C, Resistor+Inductor Load: 50hm+1mH/phase with star connection, unless otherwise noted.

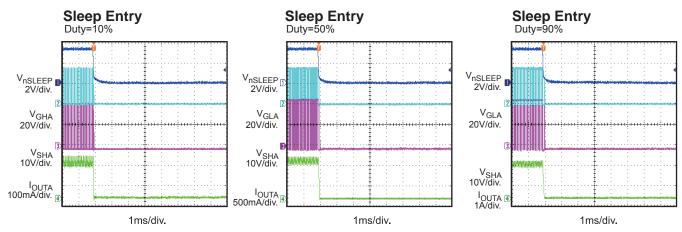


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TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 V_{IN} =24V, OC_REF=0.5V, R_{DT}=200k, DIR=H, HA=HC=H, HB=L, F_{PWM}=20kHz, T_A=25°C, Resistor+Inductor Load: 50hm+1mH/phase with star connection, unless otherwise noted.





PIN FUNCTIONS

Pin #	Name	Description
1	VREG	Gate drive supply output.
2	BSTA	Bootstrap output phase A.
3	SHA	High-side source connection phase A.
4	GHA	High-side gate drive phase A.
5	GLA	Low-side gate drive phase A.
6	BSTB	Bootstrap output phase B.
7	SHB	High-side source connection phase B.
8	GHB	High-side gate drive phase B.
9	GLB	Low-side gate drive phase B.
10	BSTC	Bootstrap output phase C.
11	SHC	High-side source connection phase C.
12	GHC	High-side gate drive phase C.
13	GLC	Low-side gate drive phase C.
14	LSS	Low-side source connection.
15	HC	Hall-sensor input, phase C.
16	HB	Hall-sensor input, phase B.
17	HA	Hall-sensor input, phase A.
18	nBRAKE	An active-low logic input for a braking function.
19	PWM	External PWM control for speed/torque.
20	DIR	A logic input to determine the direction of motor torque output.
21	nFAULT	Fault indication. Open-drain output. nFAULT is logic low when in a fault condition.
22	nSLEEP	Sleep mode input. Logic low to enter low-power sleep mode. Float to enable.
23	OC_REF	Over-current protection reference input.
24	DT	Dead time setting.
25	GND	Ground.
26	VIN	Input supply voltage.
27	CPA	Charge pump capacitor connect terminal.
28	CPB	Charge pump capacitor connect terminal.



BLOCK DIAGRAM

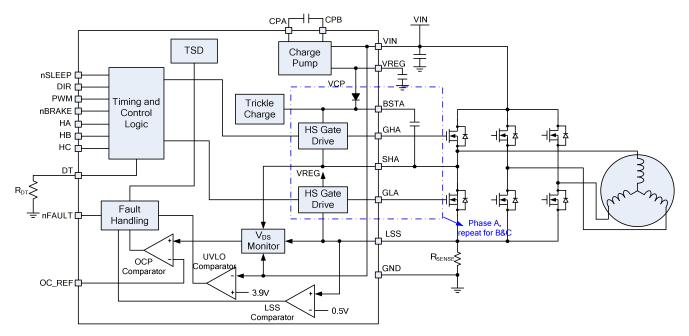


Figure 1: Functional Block Diagram



OPERATION

The MP6533 is a three-phase BLDC motor predriver that can drive three half bridges with a 0.8A source and a 1A sink current capability over a wide input voltage range of 5V to 60V. It is designed for use in battery-powered equipment. The MP6533 features a low-power sleep mode, which disables the device and draws a very low supply current.

The MP6533 provides several flexible functions, such as adjustable dead-time control and overcurrent protection, which allow the device to cover a wide range of application fields.

nFAULT

nFAULT reports to the system when a fault condition (such as OCP and OTP) is detected. nFAUIt can be an open-drain output, and it is driven low once a fault condition occurs. If the fault condition is released, nFAULT is pulled high by an external pull-up resistor.

Over-Current Protection

To protect the power stage from damage due to high currents, a VDS sensing circuitry is implemented in the MP6533. Based on R_{DS-ON} of the power MOSFETs and the maximum allowed I_{DS} , a voltage threshold can be calculated which triggers the OC protection feature when exceeded. This voltage threshold level is programmable through the OC_REF terminal by applying an external reference voltage with a DAC. Once an OCP event is detected, MP6533 will enter a latched fault state and disable all functions. MP6533 will stay latched off until it is reset by nSLEEP or UVLO.

Motor Startup Current Limit

MP6533 limits the motor startup current by monitoring the voltage at LSS pin. When the voltage at LSS exceeds the current limit threshold of 0.5V, the high side will turn off and the corresponding low side turns on for a fixed off time. After the fixed off time, the high side will turn back on and the cycle repeats until LSS no longer exceeds the current limit threshold. The current limit level is selected by the value of the current sense resistor at LSS pin.

OCP Deglitch Time

Usually, there is a current spike during the switching transition due to the body diode's reverse-recovery current or the distributed inductance or capacitance. This current spike requires filtering to prevent it from erroneously triggering OCP and shutting down the external MOSFET. An internal fixed deglitch time (t_{OC}) blanks the output of the VDS monitor when the outputs are switched (which is also the minimum on time for the MOSFET).

Dead Time Adjustment

To prevent shoot-through in any phase of the bridge, it is necessary to have a dead time (t_{DEAD}) between a high- or low-side turn-off and the next complementary turn-on event. The dead time for all three phases is set by a single dead-time resistor (R_{DT}) between DT and ground with Equation(1):

$$t_{\text{DEAD}}(nS) = 3.7^* R(k\Omega)$$
(1)

If DT is tied to GND directly, an internal minimum dead time (30ns) will be applied. Leaving DT open generates a 6µs dead time.

Input UVLO Protection

If at any time the voltage on VIN falls below the under-voltage lockout threshold voltage, all circuitry in the device is disabled and the internal logic will be reset. Operation will resume when VIN rises above the UVLO threshold.

Thermal Shutdown

If the die temperature exceeds safe limits, the MP6533 enters a latched fault state similar to an OCP event, and nFAULT is driven low. Only resetting by nSLEEP or UVLO will unlatch the device from an OTP fault lockout.

Input Logic

Driving nSLEEP low will put the device into a low-power sleep state. In this state, all the internal circuits are disabled. All inputs are ignored when nSLEEP is active low. When exiting sleep mode, a brief time period (approximately 1ms) must pass before issuing a PWM command. This time period allows the internal circuitry to stabilize.



The commutation logic is determined by three Hall-element inputs spaced at 120°. The PWM, DIR, and nBRAKE inputs are used to control motor speed/torgue, direction, and to engage brake to stop the motor.

Refer to Table 1 for the logic truth table and Table 2 for the commutation Table with nBRAKE=1. If nBRAKE=0, the braking function would be active, all low-side gates on.

PWM	nBRAKE	Mode of Operation
0	1	PWM chop mode, and the load current decays
0	0	Brake mode – All low-side gates on
1	1	Selected drivers on
1	0	Brake mode – All low-side gates on

Table 1: Input Logic Truth Table

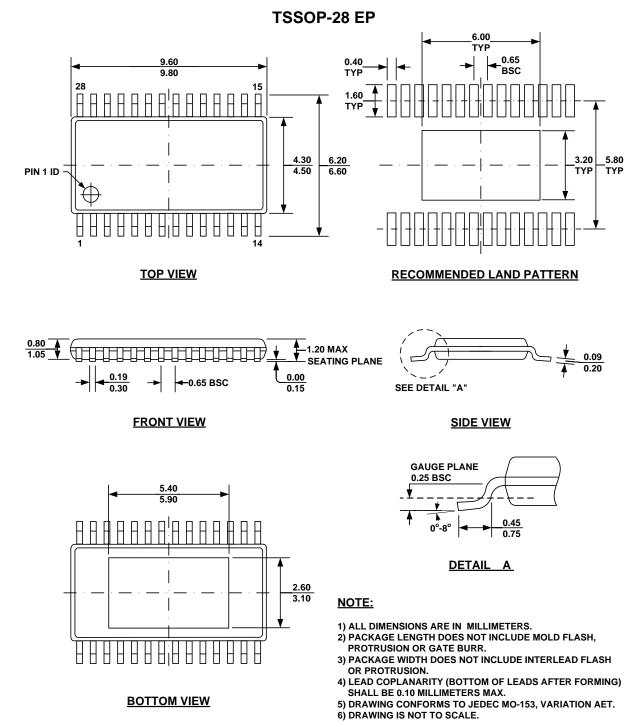
Table 2: Commutation Table (nBRAKE=1)

	Logic	Inputs		Driver Outputs					Motor Terminals			
HA	HB	HC	DIR	GLA	GLB	GLC	GHA	GHB	GHC	SHA	SHB	SHC
1	0	1	1	/PWM	0	1	PWM	0	0	Н	Z	L
1	0	0	1	0	/PWM	1	0	PWM	0	Z	Н	L
1	1	0	1	1	/PWM	0	0	PWM	0	L	Н	Z
0	1	0	1	1	0	/PWM	0	0	PWM	L	Z	Н
0	1	1	1	0	1	/PWM	0	0	PWM	Z	L	Н
0	0	1	1	/PWM	1	0	PWM	0	0	Н	L	Z
1	0	1	0	1	0	/PWM	0	0	PWM	L	Ζ	Н
1	0	0	0	0	1	/PWM	0	0	PWM	Z	L	Н
1	1	0	0	/PWM	1	0	PWM	0	0	Н	L	Z
0	1	0	0	/PWM	0	1	PWM	0	0	Н	Z	L
0	1	1	0	0	/PWM	1	0	PWM	0	Z	Н	L
0	0	1	0	1	/PWM	0	0	PWM	0	L	Н	Z

Note: If nBRAKE=0, the braking function would be active, all low-side gates on.



PACKAGE INFORMATION



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